

In the Specification:

- 1) Please insert the following heading after the title on page 1, line 6, and before the paragraph as shown below:

TECHNICAL FIELD

The invention relates to a plasma-enhanced chemical vapor deposition process, to a material containing silicon, oxygen and nitrogen, and to a layer arrangement.

- 2) Please insert the following heading on page 1, line 11, and before the paragraph as shown below:

BACKGROUND

Integrated circuit arrangements are produced with an ever greater packing density. This means that interconnects in metallizing layers have an ever shorter separation between them. In consequence, capacitances which are formed between the interconnects and lead to long signal delay times, to high power losses and to undesirable crosstalk, that is to say, which lead to an interaction between signals applied to adjacent interconnects, are increasing.

- 3) Please insert the following heading on page 4, line 3, and before the paragraph as shown below:

SUMMARY

The invention is based in particular on the problem of providing a material, a method for production of the material, and a layer arrangement with this material, which material has a sufficiently low relative dielectric constant and cannot be deposited, or can be deposited only poorly selectively, on ozone/TEOS.

4) Please insert the following heading on page 14, line 5, and before the paragraph as shown below:

BRIEF DESCRIPTION OF DRAWINGS

Exemplary embodiments of the invention will be explained in more detail in the following text and are illustrated in the figures, in which:

5) Please insert the following heading on page 14, line 39, and before the table beginning on page 15.

DETAILED DESCRIPTION